VS-HFA08TB60-M3

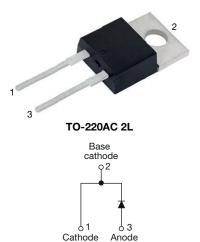
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ROHS COMPLIANT

HALOGEN

FREE

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



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PRIMARY CHARACTERISTICS						
I _{F(AV)} 8 A						
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	18 ns					
T _J max.	150 °C					
Package	TO-220AC 2L					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- \bullet Designed and qualified according to JEDEC $^{\circledast}\text{-}\mathsf{JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB60 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current	I _F	T _C = 100 °C	8				
Single pulse forward current	I _{FSM}		60	А			
Maximum repetitive forward current	I _{FRM}		24				
Maximum navyar discinction	P _D	T _C = 25 °C	36	W			
Maximum power dissipation		T _C = 100 °C	14				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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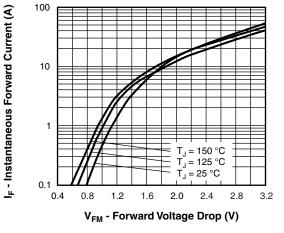
ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
		I _F = 8.0 A		-	1.4	1.7	V
Maximum forward voltage	V _{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1	
		I _F = 8.0 A, T _J = 125 °C		-	1.4	1.7	
Maximum reverse	le	$V_R = V_R$ rated	See fig. 2	-	0.3	5.0	
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	100	500	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	10	25	pF
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ c}$	A/μs, V _R = 30 V	-	18	-		
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	37	55	ns	
	t _{rr2}	T _J = 125 °C		-	55	90		
	I _{RRM1}	T _J = 25 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _B = 200 V	-	3.5	5.0	•	
Peak recovery current	I _{RRM2}	T _J = 125 °C		-	4.5	8.0	A	
	Q _{rr1}	T _J = 25 °C		-	65	138		
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	124	360	nC	
Peak rate of fall of recovery current during $t_{\rm b}$	dl _{(rec)M} /dt1	T _J = 25 °C]	-	240	-	A/uo	
	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	3.5		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-		
Weight			-	2.0	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style 2L TO-220AC		HFA08TB60			

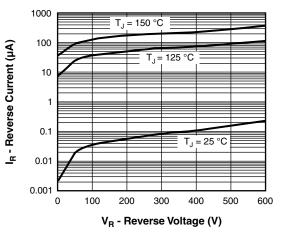
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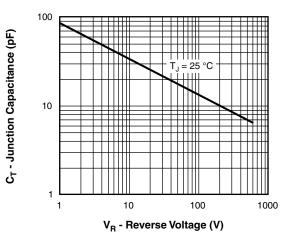


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

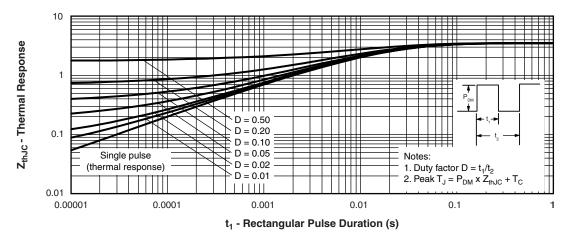
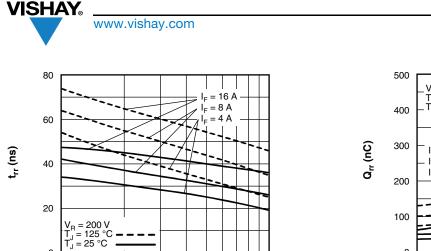


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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1000

dl_F/dt (A/µs)

Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

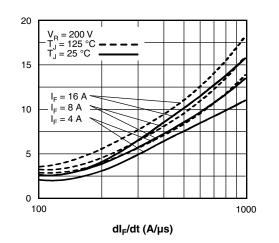
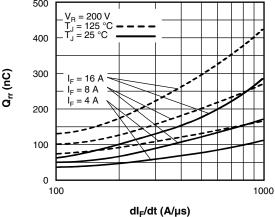


Fig. 6 - Typical Recovery Current vs. dl_F/dt





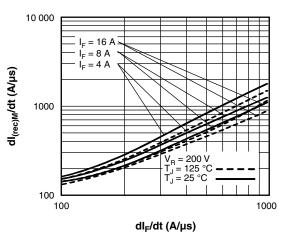


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

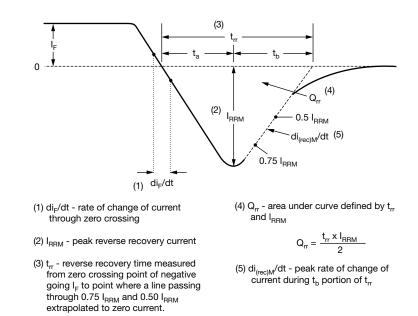


Fig. 9 - Reverse Recovery Waveform and Definitions

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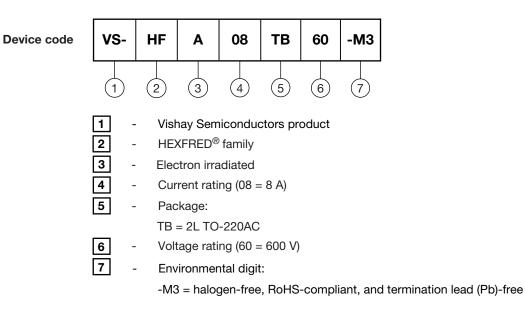
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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION						
VS-HFA08TB60-M3	50	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96156			
Part marking information	www.vishay.com/doc?95391			

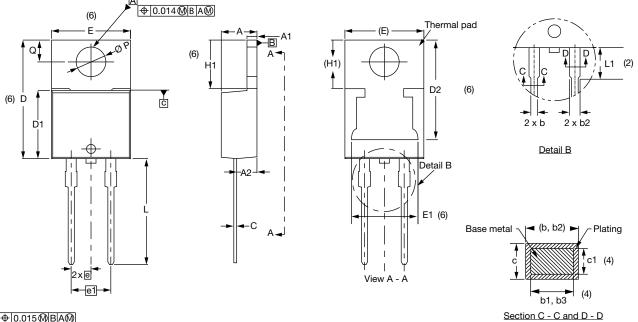




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TO-220AC 2L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC	® outline TO-220AC

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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